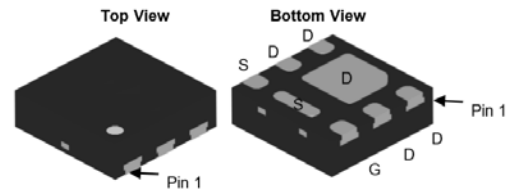


Features

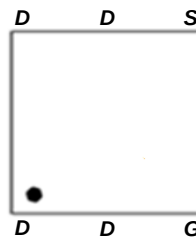
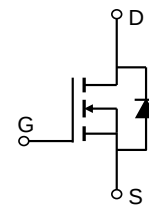
- 18V, 8A
 $R_{DS(ON)} TYP = 12m\Omega @ V_{GS} = 4.5V$
 $R_{DS(ON)} TYP = 15m\Omega @ V_{GS} = 2.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free


DFN2020-6L

Applications

- Load Switch
- PWM Application
- Power Management

100% UIS TESTED!
100% ΔV_{ds} TESTED!


Pin Assignment

Schematic Diagram

Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		18	V
V_{GS}	Gate-to-Source Voltage		± 12	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	8	A
		$T_A = 100^\circ C$	5	
I_{DM}	Pulsed Drain Current ⁽¹⁾		32	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾		36	mJ
P_D	Power Dissipation	$T_A = 25^\circ C$	2.7	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾		46	$^\circ C/W$
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	$^\circ C$

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	12	18	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 12V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	0.5	0.75	1.0	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 4.5V, I _D = 7A	-	12	16	mΩ
		V _{GS} = 2.5V, I _D = 5A	-	15	21	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 6V, f = 1MHz	-	665	-	pF
C _{oss}	Output Capacitance		-	90	-	pF
C _{rss}	Reverse Transfer Capacitance		-	80	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 4.5V V _{DD} = 6V, I _D = 2A	-	7.8	-	nC
Q _{gs}	Gate Source Charge		-	1.6	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	1.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 4.5V, V _{DD} = 6V I _D = 2A, R _{GEN} = 3Ω	-	43	-	ns
t _r	Turn-On Rise Time		-	235	-	ns
t _{d(off)}	Turn-Off DelayTime		-	677	-	ns
t _f	Turn-Off Fall Time		-	423	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	8	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 3A	-	-	1.2	V

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 10\text{V}$, $V_G = 10\text{V}$, $R_G = 25\Omega$, $L = 0.5\text{mH}$, $I_{AS} = 12\text{A}$
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit

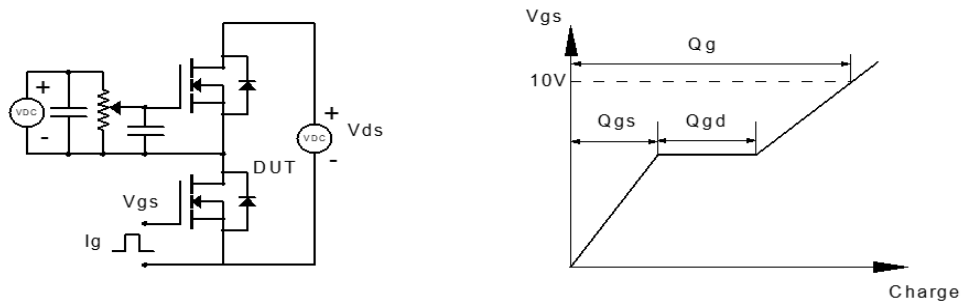


Figure 1: Gate Charge Test Circuit & Waveform

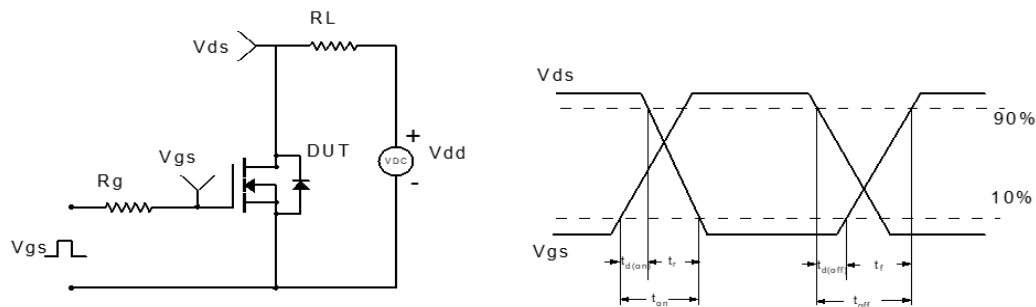


Figure 2: Resistive Switching Test Circuit & Waveform

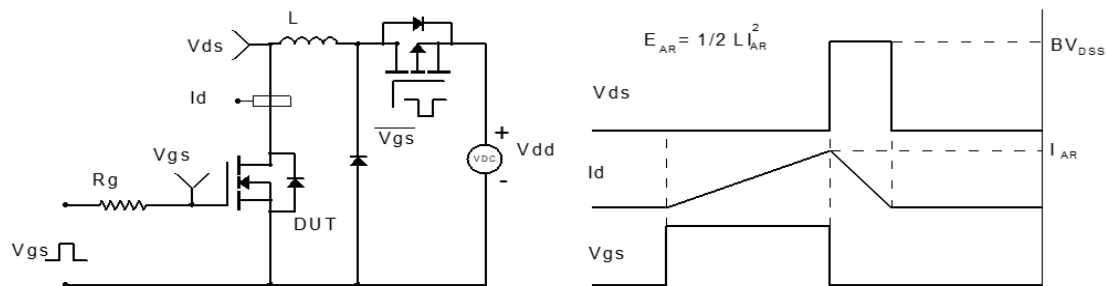


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

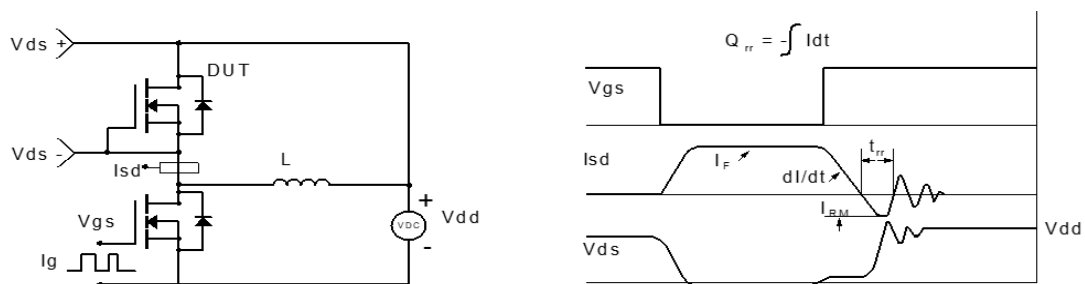
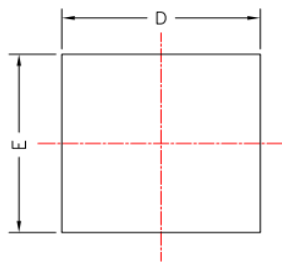
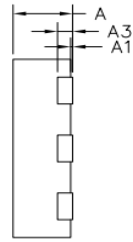


Figure 4: Diode Recovery Test Circuit & Waveform

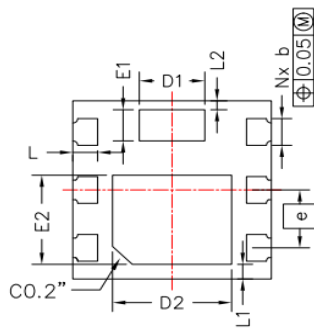
Package Mechanical Data(DFN2020-6L)



Top View



Side View



Bottom View

SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.031
A1	---	---	0.050	----	----	0.002
A3	0.195	0.203	0.211	0.008	0.008	0.008
b	0.250	0.300	0.350	0.010	0.012	0.014
e	0.65BSC			0.026 BSC		
D	1.900	2.000	2.100	0.075	0.079	0.083
E	1.900	2.000	2.100	0.075	0.079	0.083
D1	0.560	0.660	0.760	0.022	0.026	0.030
E1	0.250	0.350	0.450	0.010	0.014	0.018
D2	1.100	1.200	1.300	0.043	0.047	0.051
E2	0.900	1.000	1.100	0.035	0.039	0.043
L	0.150	0.250	0.350	0.006	0.010	0.014
L1	0.065	0.165	0.265	0.003	0.006	0.010
L2	0.000	0.100	0.200	0.000	0.004	0.008